

22. (Amended) The ferroelectric memory device according to claim 21, wherein the blocking layer comprises silicon oxynitride (SiON), silicon nitride (SiN), or aluminum oxide to prevent oxygen diffusion.

23. The ferroelectric memory device according to claim 21, wherein a diameter of the second contact hole is larger than a diameter of the first contact hole.

24. The ferroelectric memory device according to claim 21, wherein the buried contact structure is made of tungsten (W).